

GaN Amplifier 32 V, 8 W

3.3 - 4.2 GHz



MACOM PURE CARBIDE™

MAPC-A2025

Rev. V1

Features

- MACOM PURE CARBIDE™ Amplifier Series
- Optimized for 3.3 - 4.2 GHz Applications
- High Terminal Impedances for Broadband Performance
- 26 - 36 V Operation
- Low Thermal Resistance
- 100% RF Tested
- RoHS* Compliant



4 mm QFN

Applications

- 5G Cellular Networks
- Tri-band Small Cells

Description

The MAPC-A2025 is a GaN on Silicon Carbide HEMT D-mode amplifier suitable for applications 1W average power and optimized for 3.3 - 4.2 GHz modulated signal operation. The device supports pulsed, and linear operation with peak output power levels to 8 W (39 dBm) in an 4 mm surface mount QFN package.

Typical Doherty Performance:

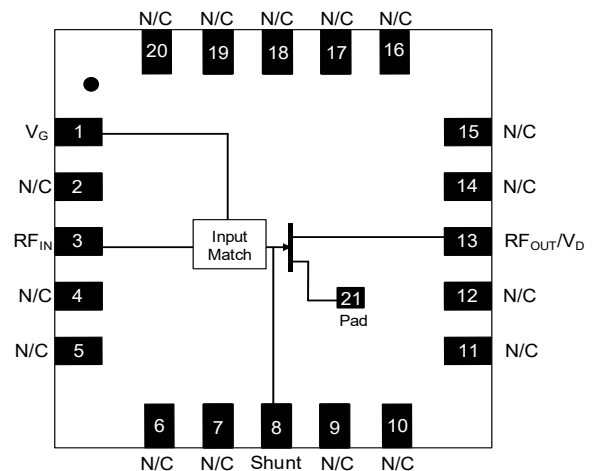
- WCDMA 3GPP TM1, 10 dB PAR @ 0.01% CCDF. $V_{DS} = 32$ V, $I_{DQ} = 60$ mA, $T_C = 25^\circ\text{C}$, $P_{OUT} = 32$ dBm

Frequency (GHz)	GP (dB)	η_D (%)	Output PAR (dB)	ACPR (dBc)
3.3	16.3	36	6.8	-33.3
3.6	16.0	32	7.6	-37.1
3.9	16.4	32	7.6	-37.3
4.2	16.5	35	6.9	-32.9

Ordering Information

Part Number	Package
MAPC-A2025-AQ000	Bulk Quantity
MAPC-A2025-AQTR1	Tape and Reel
MAPC-A2025-AQSB1	Sample Board

Functional Schematic



Pin Configuration

Pin #	Pin Name	Function
1	V_G	Gate Voltage
2, 4-7, 9-12, 14-20	N/C	Not Connected
3	RF_{IN}	RF Input
8	SHUNT	Gate Shunt Capacitor
13	RF_{OUT} / V_D	RF Output / Drain Voltage
21	Pad ¹	Ground / Source

1. The pad on the package bottom must be connected to RF, DC and thermal ground.

1 * Restrictions on Hazardous Substances, compliant to current RoHS EU directive.

GaN Amplifier 32 V, 8 W

3.3 - 4.2 GHz



MACOM PURE CARBIDE™

MAPC-A2025

Rev. V1

RF Electrical Characteristics: $T_C = 25^\circ\text{C}$, $V_{DS} = 32\text{ V}$, $I_{DQ} = 60\text{ mA}$

Note: Performance in MACOM Single-ended Class-AB Evaluation Circuit, 50 Ω system.

Parameter	Test Conditions	Symbol	Min.	Typ.	Max.	Units
Small Signal Gain	Pulsed ² , 4.2 GHz	G_{SS}	-	18.0	-	dB
Saturated Output Power	Pulsed ² , 4.2 GHz	P_{SAT}	-	38.0	-	dBm
Drain Efficiency at Saturation	Pulsed ² , 4.2 GHz	η_{SAT}	-	59	-	%
Modulated Peak Power	WCDMA ³ , 4.2 GHz	$P_{2.5dB}^4$	-	38.7	-	dBm
Gain Flatness in 60MHz	WCDMA ³ , $P_{OUT} = 32\text{ dBm}$	G_F	-	0.1	-	dB
Gain Variation (-25°C to +105°C)	WCDMA ³ , 4.2 GHz, $P_{OUT} = 32\text{ dBm}$	ΔG	-	0.013	-	dB/°C
Power Variation (-25°C to +105°C)	Pulsed ² , 4.2 GHz	$\Delta P_{2.5dB}$	-	0.006	-	dBm/°C
Power Gain	WCDMA ³ , 4.2 GHz, $P_{OUT} = 32\text{ dBm}$	G_P	-	16.5	-	dB
Drain Efficiency	WCDMA ³ , 4.2 GHz, $P_{OUT} = 32\text{ dBm}$	η	-	35	-	%
Output CCDF @ 0.01%	WCDMA ³ , 4.2 GHz, $P_{OUT} = 32\text{ dBm}$	PAR	-	6.9	-	dB
Adjacent Channel Power	WCDMA ³ , 4.2 GHz, $P_{OUT} = 32\text{ dBm}$	ACP	-	-32.9	-	dBc
Input Return Loss	WCDMA ³ , 4.2 GHz, $P_{OUT} = 32\text{ dBm}$	IRL	-	-9	-	dB
Ruggedness: Output Mismatch	All phase angles	Ψ	VSWR = 10:1, No Device Damage			

2. Pulse details: 100 μs pulse width, 1 ms period, 10% Duty Cycle

3. Modulated Signal: 3.84MHz, WCDMA 3GPP TM1 64 DPCH, 9.9 dB PAR @ 0.01% CCDF

4. $P_{2.5dB} = P_{OUT} + 7.5\text{ dB}$ where P_{OUT} is the average output power measured using a modulated signal⁵ where the output PAR is compressed to 7.5 dB @ 0.01% probability CCDF.

RF Electrical Characteristics: $T_A = 25^\circ\text{C}$, $V_{DS} = 32\text{ V}$, $I_{DQ} = 60\text{ mA}$

Note: Performance in MACOM Single-ended Class-AB Production Test Fixture, 50 Ω system.

Parameter	Test Conditions	Symbol	Min.	Typ.	Max.	Units
Power Gain	WCDMA ³ , 4.2 GHz, $P_{OUT} = 33\text{ dBm}$	G_P	13.0	13.9	-	dB
Drain Efficiency	WCDMA ³ , 4.2 GHz, $P_{OUT} = 33\text{ dBm}$	η	21.5	25.0	-	%
Output CCDF @ 0.01%	WCDMA ³ , 4.2 GHz, $P_{OUT} = 33\text{ dBm}$	PAR	7.0	7.4	-	dB
Input Return Loss	WCDMA ³ , 4.2 GHz, $P_{OUT} = 33\text{ dBm}$	IRL	-	-13.3	-	dB

DC Electrical Characteristics: $T_C = 25^\circ\text{C}$

Parameter	Test Conditions	Symbol	Min.	Typ.	Max.	Units
Drain-Source Leakage Current	$V_{GS} = -8\text{ V}$, $V_{DS} = 100\text{ V}$	I_{DLK}	-	-	1.4	mA
Gate-Source Leakage Current	$V_{GS} = -8\text{ V}$, $V_{DS} = 0\text{ V}$	I_{GLK}	-	-	-1.4	mA
Gate Threshold Voltage	$V_{DS} = 32\text{ V}$, $I_D = 1.4\text{ mA}$	V_T	-	-2.9	-	V
Gate Quiescent Voltage	$V_{DS} = 32\text{ V}$, $I_D = 60\text{ mA}$	V_{GSQ}	-	-2.4	-	V
Maximum Drain Current	$V_{DS} = 7\text{ V}$, pulse width 300 μs	$I_{D,MAX}$	-	1.2	-	A

Absolute Maximum Ratings^{5,6,7,8,9}

Parameter	Absolute Maximum
Drain Source Voltage, V_{DS}	100 V
Gate Source Voltage, V_{GS}	-10 to 3 V
Gate Current, I_G	1.4 mA
Storage Temperature Range	-65°C to +150°C
Case Operating Temperature Range	-40°C to +120°C
Channel Operating Temperature Range, T_{CH}	-40°C to +225°C
Absolute Maximum Channel Temperature	+250°C

5. Exceeding any one or combination of these limits may cause permanent damage to this device.
6. MACOM does not recommend sustained operation above maximum operating conditions.
7. Operating at drain source voltage $V_{DS} < 36$ V will ensure $MTTF > 2.51 \times 10^6$ hours.
8. Operating at nominal conditions with $T_{CH} \leq 225^\circ\text{C}$ will ensure $MTTF > 2.51 \times 10^6$ hours.
9. MTTF may be estimated by the expression $MTTF \text{ (hours)} = A e^{\frac{B}{C(T+273)}}$ where T is the channel temperature in degrees Celsius., $A = 1.93$, $B = -45.31$, and $C = 29,585$.

Thermal Characteristics¹⁰

Parameter	Test Conditions	Symbol	Typical	Units
Thermal Resistance using Finite Element Analysis	$V_{DS} = 32$ V $T_C = 85^\circ\text{C}$, $T_{CH} = 225^\circ\text{C}$	$R_{\theta}(\text{FEA})$	14.7	°C/W

10. Case temperature measured using thermocouple embedded in heat-sink. Contact local applications support team for more details on this measurement.

Handling Procedures

Please observe the following precautions to avoid damage:

Static Sensitivity

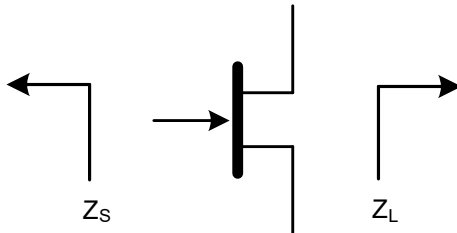
Gallium Nitride Circuits are sensitive to electrostatic discharge (ESD) and can be damaged by static electricity. Proper ESD control techniques should be used when handling these devices.

**Pulsed² Load-Pull Performance
Reference Plane at Device Leads**

Frequency (GHz)	Z_{SOURCE} (Ω)	Maximum Output Power					
		$V_{DS} = 32\text{ V}, I_{DQ} = 48\text{ mA}, T_C = 25^\circ\text{C}, P_{2.5dB}$					
		Z_{LOAD}^{11} (Ω)	Gain (dB)	P_{OUT} (dBm)	P_{OUT} (W)	η_D (%)	AM/PM ($^\circ$)
3.3	94.6 - j10.5	34.9 + j8.9	14.6	39.3	8.5	47.4	-50.9
3.7	58.0 + j27.5	32.3 + j8.3	14.5	38.9	7.8	49.5	-89.4
4.0	34.1 + j24.3	25.1 + j7.0	15.0	39.2	8.3	53.9	-100.5
4.2	31.1 + j17.3	23.9 + j3.4	14.9	38.9	7.8	49.8	-112.6

Frequency (GHz)	Z_{SOURCE} (Ω)	Maximum Drain Efficiency					
		$V_{DS} = 32\text{ V}, I_{DQ} = 48\text{ mA}, T_C = 25^\circ\text{C}, P_{2.5dB}$					
		Z_{LOAD}^{12} (Ω)	Gain (dB)	P_{OUT} (dBm)	P_{OUT} (W)	η_D (%)	AM/PM ($^\circ$)
3.3	82.4 + j23.7	24.4 + j24.4	16.0	38.0	6.3	54.1	-62.8
3.7	43.4 + j31.9	22.3 + j19.1	16.0	38.1	6.5	53.6	-89.4
4.0	24.3 + j20.2	18.0 + j14.0	16.2	38.6	7.2	59.2	-109.7
4.2	23.9 + j11.9	18.1 + j11.5	16.0	38.4	6.9	55.5	-124.3

Impedance Reference



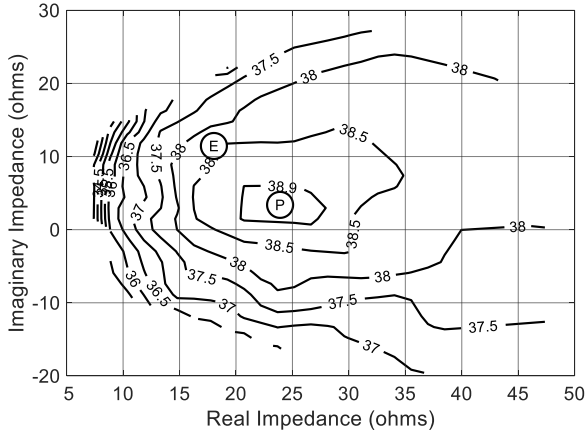
Z_{SOURCE} = Measured impedance presented to the input of the device at package reference plane.

Z_{LOAD} = Measured impedance presented to the output of the device at package reference plane.

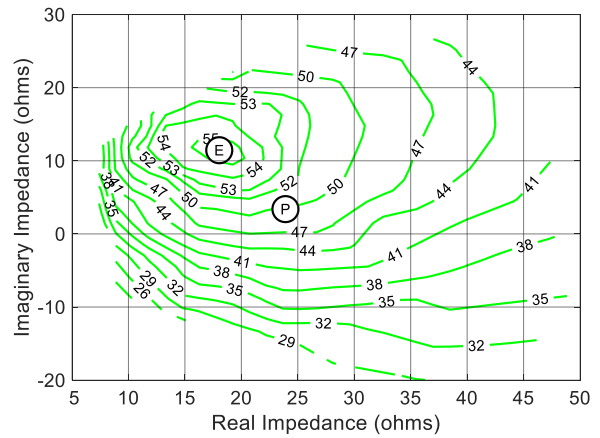
- 11. Load Impedance for optimum output power.
- 12. Load Impedance for optimum efficiency.

Pulsed² Load-Pull Performance
4.2GHz

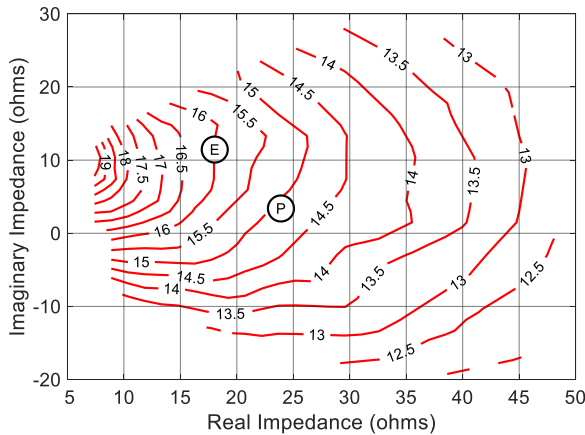
P2.5dB Loadpull Output Power Contours (dBm)



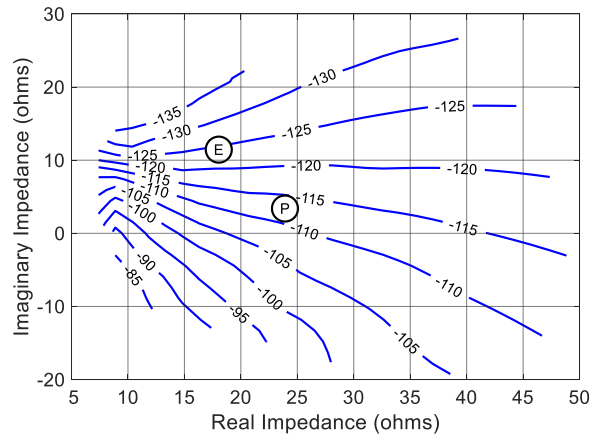
P2.5dB Loadpull Drain Efficiency Contours (%)



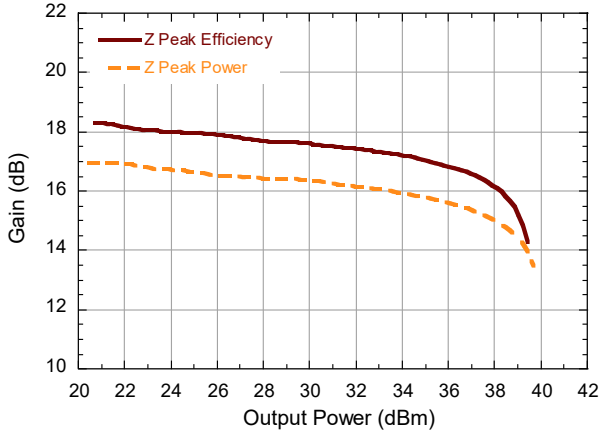
P2.5dB Loadpull Gain Contours (dB)



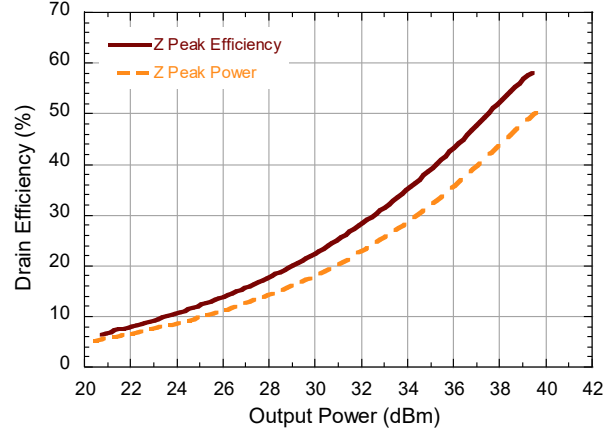
P2.5dB Loadpull AM/PM Contours (°)



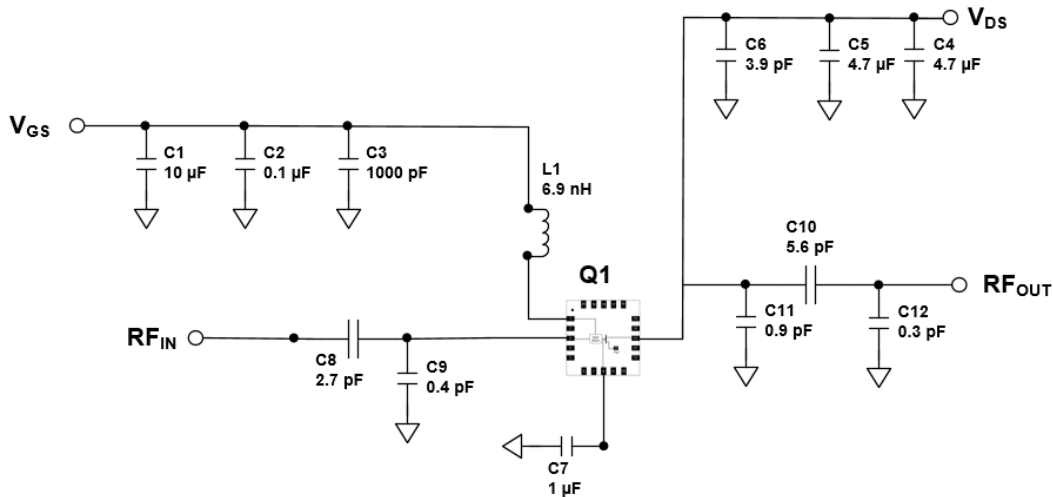
Gain vs. Output Power



Drain Efficiency vs. Output Power



Evaluation Test Fixture and Recommended Tuning Solution 3.3 - 4.2 GHz



Description

Parts measured on evaluation board (20-mil thick RO4350). Matching is provided using a combination of lumped elements and transmission lines as shown in the simplified schematic above. Recommended tuning solution component placement, transmission lines, and details are shown on the next page.

Bias Sequencing

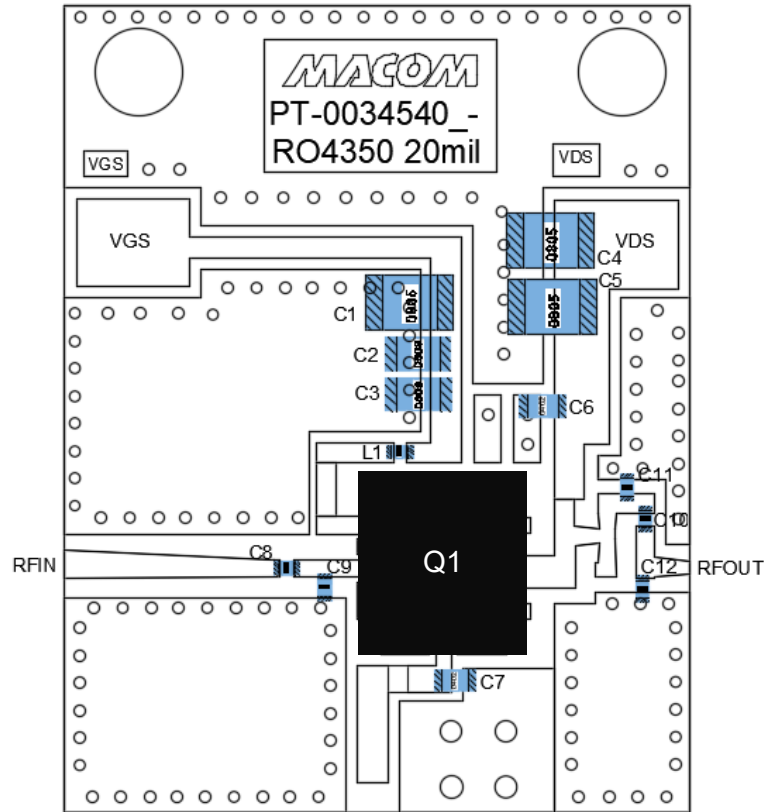
Turning the device ON

1. Set V_{GS} to pinch-off (V_P).
2. Turn on V_{DS} to nominal voltage (32 V).
3. Increase V_{GS} until I_{DS} current is reached.
4. Apply RF power to desired level.

Turning the device OFF

1. Turn the RF power OFF.
2. Decrease V_{GS} down to V_P pinch-off.
3. Decrease V_{DS} down to 0 V.
4. Turn off V_{GS} .

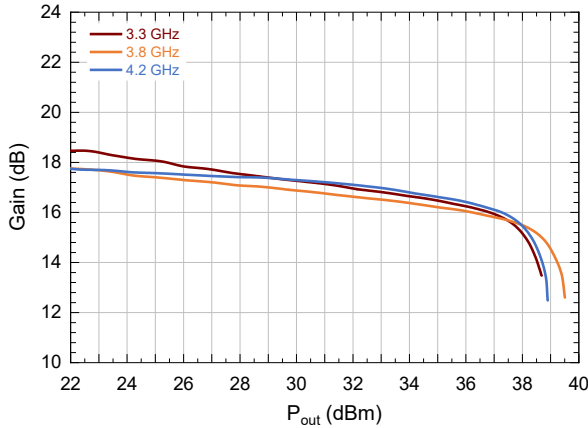
Evaluation Board and Recommended Tuning Solution 3.3 - 4.2 GHz



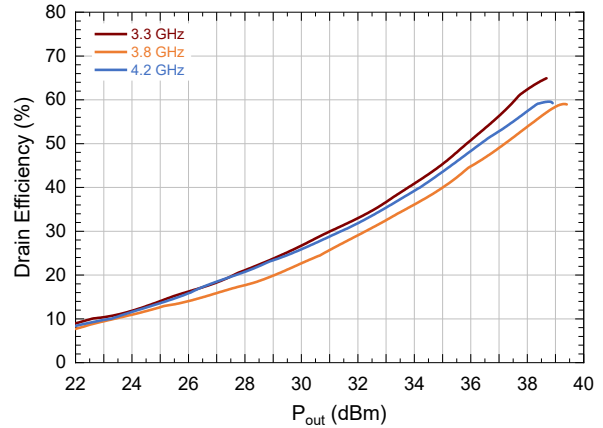
Reference Designator	Value	Tolerance	Manufacturer	Part Number
C1	10 μ F	+/- 20%	TDK Corporation	C2012X5R1C106M085AC
C2	0.1 μ F	+/- 10%	Murata	GCM21BR72A104KA37L
C3	1000 pF	+/- 5%	Murata	GRM1555C1H102JA01D
C4, C5	4.7 μ F	+/- 10%	Murata	GRM21BC81H475KE11L
C6	3.9 pF	+/- 0.05pF	Murata	GQM1555C2D3R9WB01D
C7	1 μ F	+/- 10%	Murata	GRM155Z71A105KE01D
C8	2.7 pF	+/- 0.05 pF	Murata	GQM0335C2D2R7WB01D
C9	0.4 pF	+/- 5%	Murata	GQM0335C2DR40WB01D
C10	5.6 pF	+/- 10%	Murata	GQM0335C2D5R6WB01D
C11	0.9 pF	+/- 5%	Murata	GQM0335C2DR90WB01D
C12	0.3 pF	+/- 5%	Murata	GQM0335C2DR30WB01D
L1	6.9 nH	+/- 10%	Coilcraft	0201DS-6N9X.JE
Q1			MACOM	MAPC-A2025
PCB	RO4350, 20 mil, 1 oz Cu, Tin Lead Finish			

Typical Performance Curves as Measured in the 3.3 - 4.2 GHz Evaluation Board:
Pulsed² 3.8 GHz, $V_{DS} = 32$ V, $I_{DQ} = 60$ mA, $T_C = 25^\circ\text{C}$

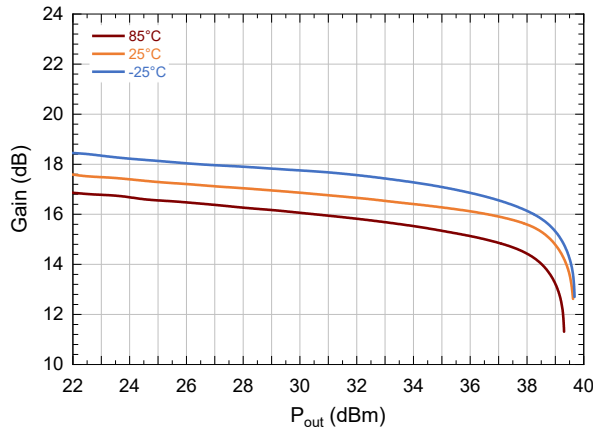
Gain vs. Output Power and Frequency



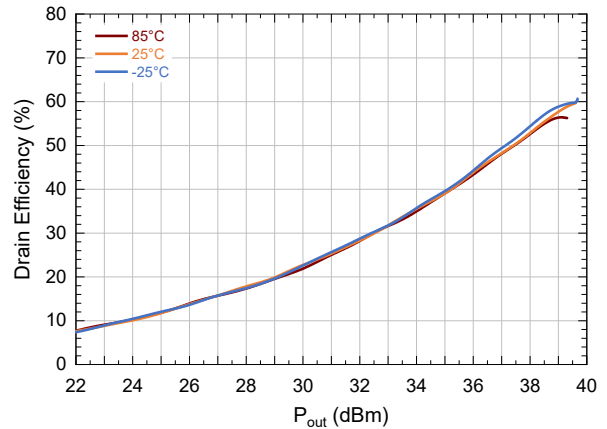
Drain Efficiency vs. Output Power and Frequency



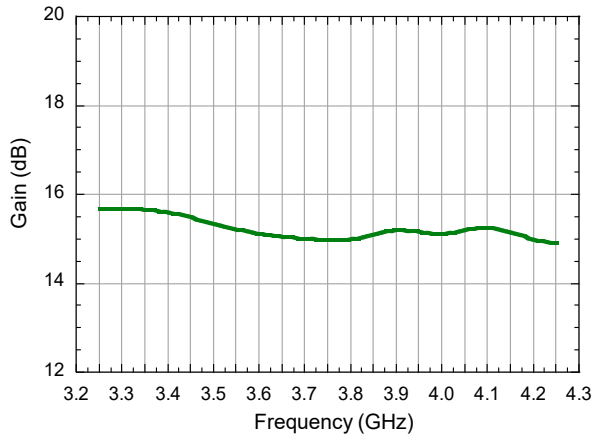
Gain vs. Output Power and T_C



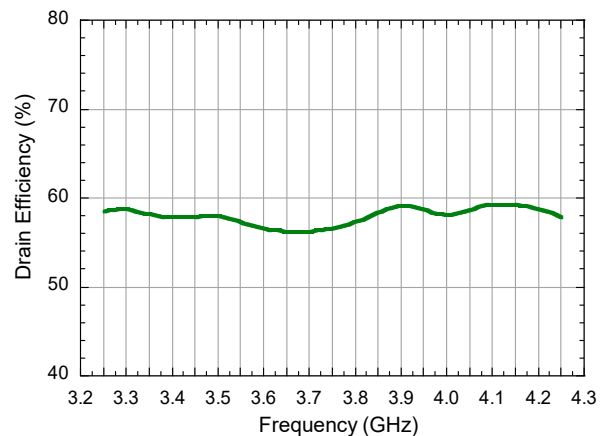
Drain Efficiency vs. Output Power and T_C



Gain vs. Frequency, 3dB Gain Compression

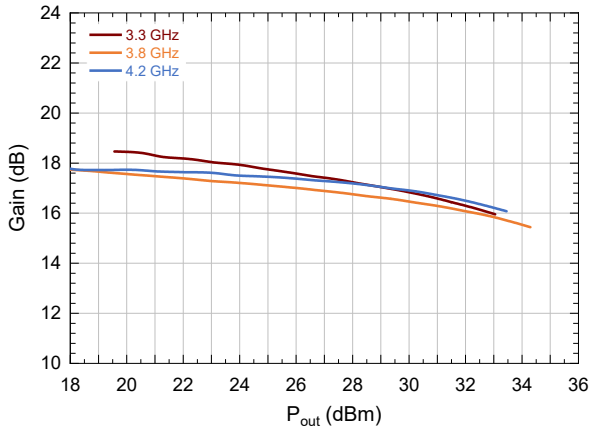


Drain Efficiency vs. Frequency, 3dB Gain Compression

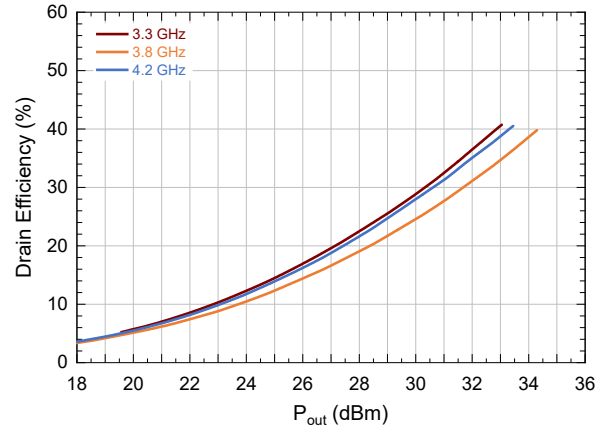


Typical Performance as Measured in the 3.3 - 4.2 GHz Evaluation Board:
WCDMA 3GPP TM1 64 DPCH 9.9 dB PAR @ 0.01% CCDF, $V_{DS} = 32\text{ V}$, $I_{DQ} = 60\text{ mA}$, $T_C = 25\text{ }^\circ\text{C}$

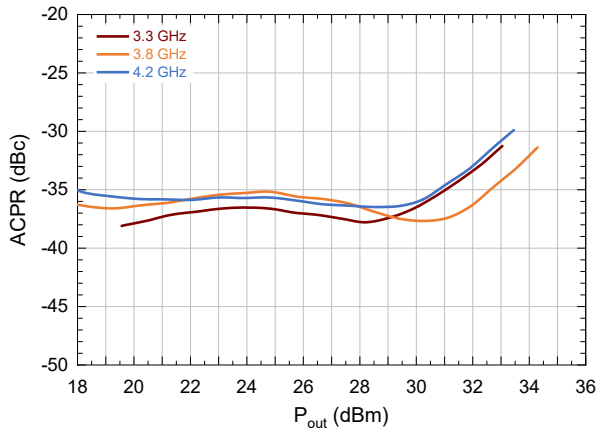
Gain vs. Output Power and Frequency



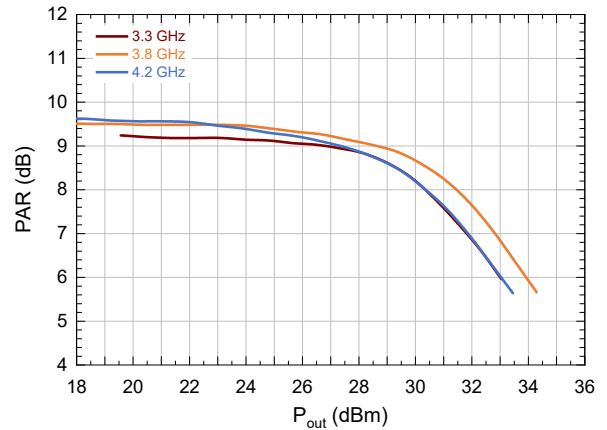
Drain Efficiency vs. Output Power and Frequency



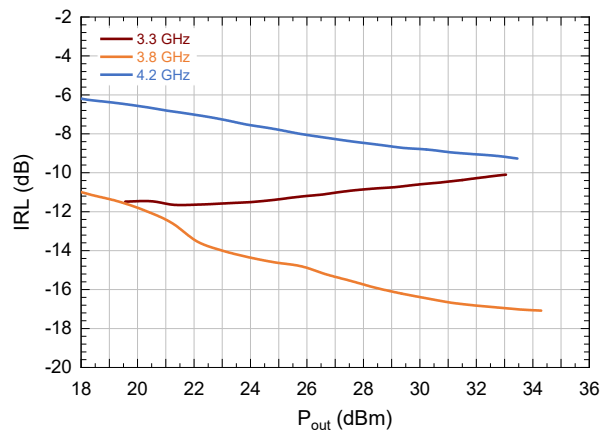
ACPR (Max $\pm 5\text{ MHz}$) vs. Output Power and Frequency



PAR (CCDF @ 0.01%) vs. Output Power and Frequency

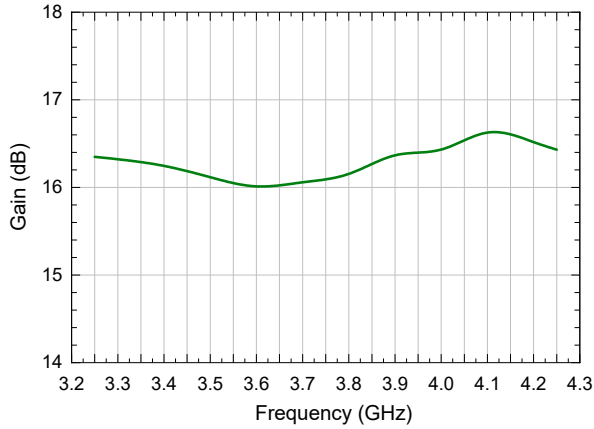


Input Return Loss vs. Output Power and Frequency

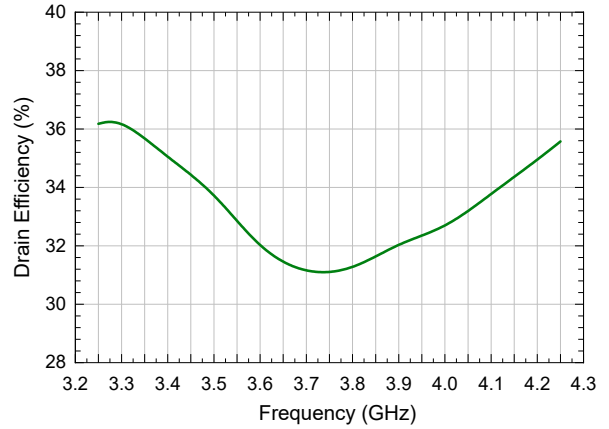


Typical Performance as Measured in the 3.3 - 4.2 GHz Evaluation Board:
WCDMA 3GPP TM1 64 DPCH 9.9 dB PAR @ 0.01% CCDF, $V_{DS} = 32\text{ V}$, $I_{DQ} = 60\text{ mA}$, $T_C = 25^\circ\text{C}$

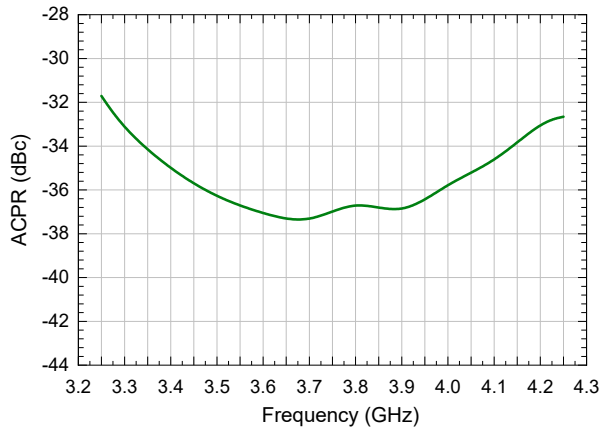
Gain vs. Frequency at $P_{OUT} = 32\text{ dBm}$



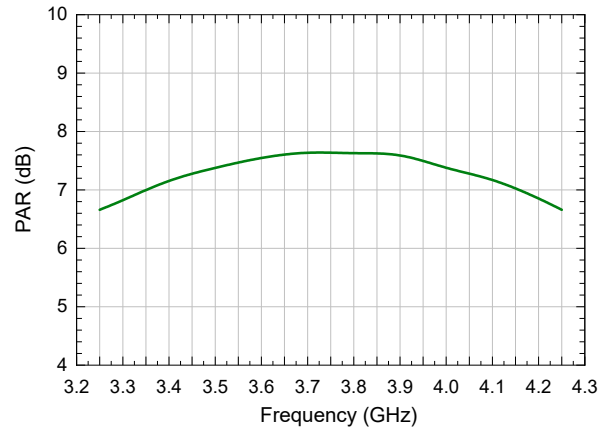
Drain Efficiency vs. Frequency at $P_{OUT} = 32\text{ dBm}$



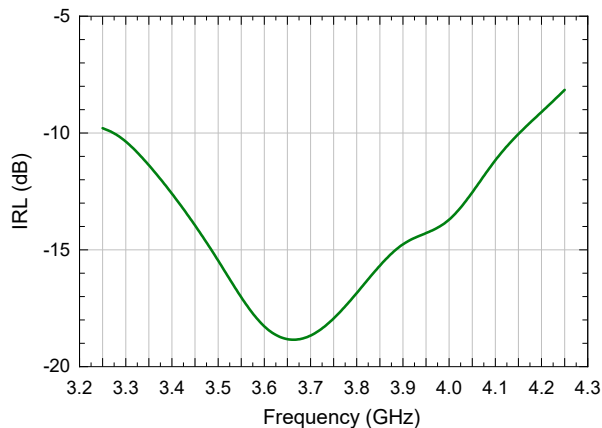
ACPR (Max $\pm 5\text{ MHz}$) vs. Frequency at $P_{OUT} = 32\text{ dBm}$



PAR (CCDF @ 0.01%) vs. Frequency at $P_{OUT} = 32\text{ dBm}$



Input Return Loss vs. Frequency at $P_{OUT} = 32\text{ dBm}$



GaN Amplifier 32 V, 8 W
3.3 - 4.2 GHz

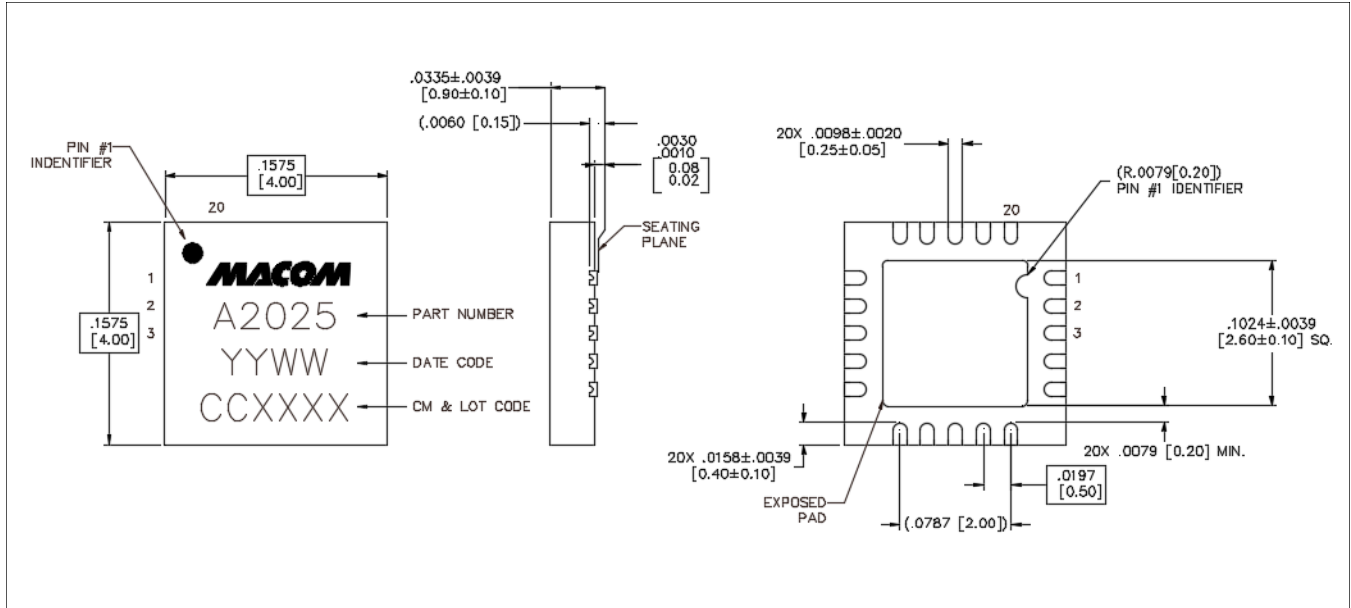


MACOM PURE CARBIDE™

MAPC-A2025

Rev. V1

Lead-Free 4 mm 20-Lead Package Dimensions†



† Reference Application Note AN0004363 for lead-free solder reflow recommendations.
Meets JEDEC moisture sensitivity level 3 requirements.
Plating is NiPdAu

MACOM Technology Solutions Inc. ("MACOM"). All rights reserved.

These materials are provided in connection with MACOM's products as a service to its customers and may be used for informational purposes only. Except as provided in its Terms and Conditions of Sale or any separate agreement, MACOM assumes no liability or responsibility whatsoever, including for (i) errors or omissions in these materials; (ii) failure to update these materials; or (iii) conflicts or incompatibilities arising from future changes to specifications and product descriptions, which MACOM may make at any time, without notice. These materials grant no license, express or implied, to any intellectual property rights.

THESE MATERIALS ARE PROVIDED "AS IS" WITH NO WARRANTY OR LIABILITY, EXPRESS OR IMPLIED, RELATING TO SALE AND/OR USE OF MACOM PRODUCTS INCLUDING FITNESS FOR A PARTICULAR PURPOSE, MERCHANTABILITY, INFRINGEMENT OF INTELLECTUAL PROPERTY RIGHT, ACCURACY OR COMPLETENESS, OR SPECIAL, INDIRECT, INCIDENTAL, OR CONSEQUENTIAL DAMAGES WHICH MAY RESULT FROM USE OF THESE MATERIALS.

MACOM products are not intended for use in medical, lifesaving or life sustaining applications. MACOM customers using or selling MACOM products for use in such applications do so at their own risk and agree to fully indemnify MACOM for any damages resulting from such improper use or sale.